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IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

JAN - 3 2003

In re the Application of:

TECHNOLOGY CENTER 2800

NIKAMI, Takashi

Group Art Unit: 2811

Serial No.: 10/084,925 ✓

Examiner: VU, Quang D.

Filed: March 1, 2002 ✓

P.T.O. Confirmation No.: 7137

For: SEMICONDUCTOR DEVICE AND METHOD FOR FABRICATING THE SAME

AMENDMENT UNDER 37 CFR §1.111

Commissioner for Patents
Washington, D.C. 20231

January 2, 2003

Sir:

In response to the Office Action dated October 3, 2002, please amend the above-identified application as follows:

IN THE CLAIMS: ✓

Please **CANCEL** claims 5 and 10-12 without prejudice or disclaimer.

Please **AMEND** the claims as follows:

1. (Amended) A semiconductor device, comprising:
- 2 a source region formed of a semiconductor;
 - 3 a drain region formed of a semiconductor of the same conductive type as that of said source region;
 - 4 a channel region formed of a semiconductor between said source region and said drain region;
 - 5 a gate insulating film provided on said channel region; and